

197802US-2S

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

WAKAKO MORIYAMA ET AL : EXAMINER: LEE, G. D.

SERIAL NO: 09/670,520 :

FILED: SEPTEMBER 26, 2000 : GROUP ART UNIT: 2825

FOR: METHOD FOR MANUFACTURING  
SEMICONDUCTOR DEVICES  
USING THERMAL NITRIDE FILMS  
AS GATE INSULATING FILMSAMENDMENTASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

In response to the Official Action mailed December 17, 2002, please amend this application as follows:

IN THE SPECIFICATION

Please amend the specification to read as follows:<sup>1</sup>

Page 6, lines 2-10, please replace the paragraph with the following text:

According to an aspect of the present invention, there is provided a semiconductor device manufacturing method comprising forming a gate insulating film in an oxynitride form on a main surface of a semiconductor substrate; forming gate electrodes on the gate insulating film; removing the gate insulating film except under the gate electrodes to expose

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<sup>1</sup>A marked-up copy of the changes made to the specification is attached.